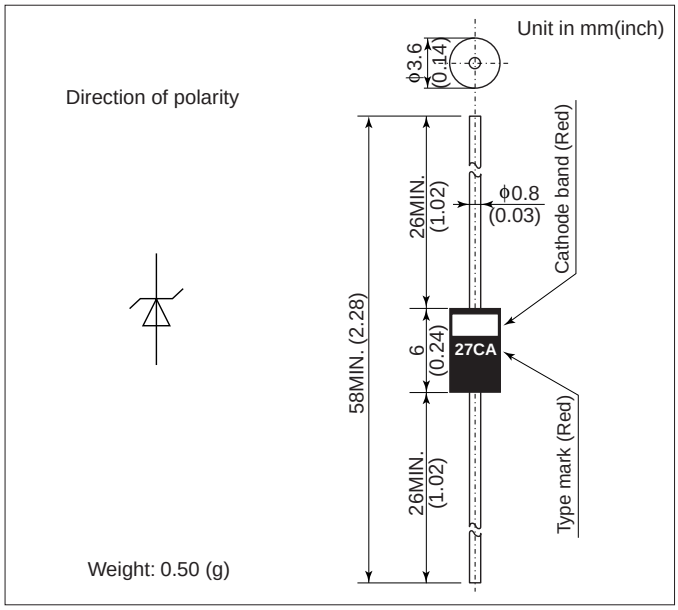
DAM3B

FEATURES

- High transient reverse power capability suitable for protecting automobile electronic components etc.
- Diffused-junction. Resin encapsulated.

OUTLINE DRAWING



ABSOLUTE MAXIMUM RATINGS

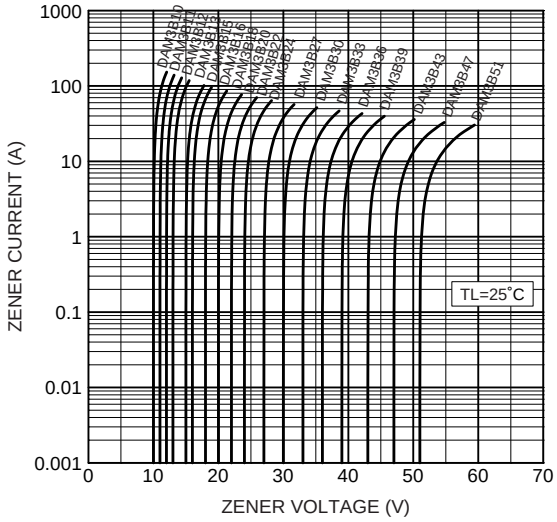
Items	Symbols	Units	Ratings
Non-Repetitive Peak Reverse One-Cycle Dissipation	P_{RSM}	W	1800(Rectangular pulse t=0.1ms T_i=25°C start)
Operating Junction Temperature	T_j	°C	-40 ~ +150
Storage Temperature	T_{stg}	°C	-40 ~ +150
DC Reverse Voltage	V_{DC}	V	Refer to characteristics column

CHARACTERISTICS(T_L=25°C)

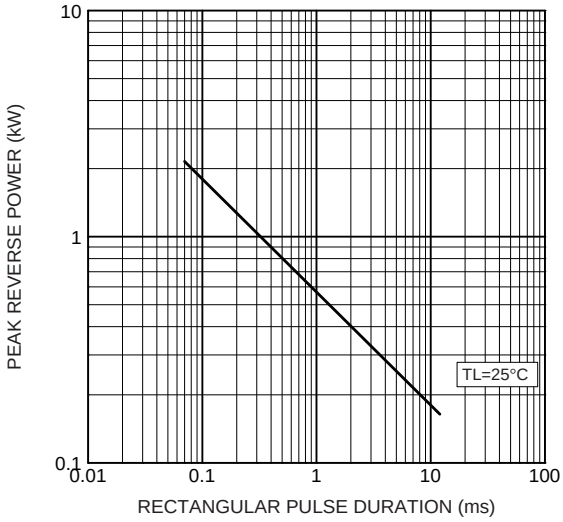
Type	DC Reverse Voltage V_{DC} (V)	Characteristics				Maximum Reverse Current	
		Zener Voltage Vz (V)		Maximum Dynamic Impedance Zz (ohm)	Test Current Iz (mA)	I_{RRM} (μA)	V_R (V)
		Minimum	Maximum				
DAM3B10	7	9.4	10.6	15	75	50	7
DAM3B11	8	10.4	11.6	15	75	50	8
DAM3B12	9	11.4	12.7	15	75	50	9
DAM3B13	10	12.4	14.1	15	75	50	10
DAM3B15	11	13.5	15.6	15	75	50	11
DAM3B16	12	15.3	17.1	15	75	50	12
DAM3B18	13	16.8	19.1	15	45	50	13
DAM3B20	14	18.8	21.2	15	45	50	14
DAM3B22	16	20.8	23.3	15	45	50	16
DAM3B24	18	22.7	25.6	15	30	50	18
DAM3B27	20	25.1	28.9	15	30	50	20
DAM3B30	22	28.0	32.0	15	30	50	22
DAM3B33	24	31.0	35.0	15	30	50	24
DAM3B36	26	33.4	38.6	15	30	50	26
DAM3B39	28	36.1	41.9	15	30	50	28
DAM3B43	31	39.8	46.2	30	20	50	31
DAM3B47	34	43.3	50.7	30	20	50	34
DAM3B51	37	46.9	55.1	30	20	50	37

DAM3B

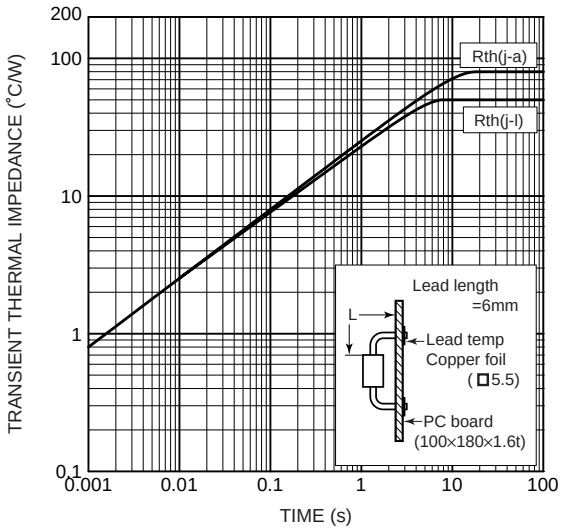
Typical zener characteristics



Typical reverse power characteristic
(Rectangular pulse non-repetitive)



Transient thermal impedance



HITACHI POWER SEMICONDUCTORS

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